Analog Power AM2328NE

N-Channel 20V (D-S) MOSFET

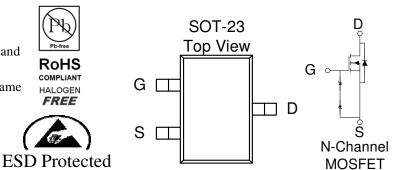
FREE

2000V

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low r_{DS(on)} and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(\Omega)$	$I_{D}(A)$		
20	$0.018 @ V_{GS} = 4.5 V$	7.0		
	$0.021 @ V_{GS} = 2.5V$	6.5		

- Low $r_{DS(on)} \, \text{provides higher efficiency} \, \, \text{and} \,$ extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Paramete r		Symbol	Maximum	Units	
Drain-Source Voltage			20	V	
Gate-Source Voltage			±8	V	
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	 -T	7.0		
Continuous Drain Current	$T_A=70^{\circ}C$	П	5.7	A	
Pulsed Drain Current ^b			DM ±20		
Continuous Source Current (Diode Conduction) ^a		I_S	1.6	A	
Daniel Diagram 4 in a	$T_A=25^{\circ}C$	P_{D}	1.3	W	
Power Dissipation ^a	$T_A=25$ °C $T_A=70$ °C	L D	0.9		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
N. T	t <= 5 sec	D	100	0000	
Maximum Junction-to-Ambient ^a	Steady-State	R_{THJA}	166	C/W	

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Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Danamatan	C	T. 4 C. 111	Limits			T 1:4
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.4			V
Gate-Body Leakage	${ m I}_{ m GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	μΑ
Zero Gate Voltage Drain Current	ī	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μА
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α
Drain-Source On-Resistance ^A		$V_{GS} = 4.5 \text{ V}, I_D = 1 \text{ A}$			18	mΩ
Drain-Source On-Resistance	$r_{ m DS(on)}$	$V_{GS} = 2.5 \text{ V}, I_D = 1 \text{ A}$			21	
Forward Tranconductance ^A	$g_{ m fs}$	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ A}$		11.3		S
Diode Forward Voltage	V_{SD}	$I_S = 1 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V
Dynamic ^b						
Total Gate Charge	Q_{g}			13.4		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		0.9		пC
Gate-Drain Charge	Q_{gd}			2.0		1
Turn-On Delay Time	$t_{d(on)}$			8		
Rise Time	t _r	$V_{DD} = 10 \text{ V}, R_L = 15 \Omega, I_D = 1 \text{ A},$		24]
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 4.5 \text{ V}$		35		ns
Fall-Time	t_{f}			10		

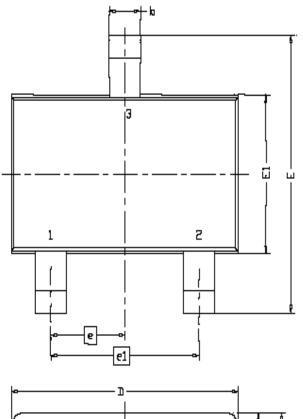
Notes

a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

b. Guaranteed by design, not subject to production testing.

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Package Information



DIM.	MILLIMETERS			
יהודת	MIN	NDM	MAX	
Α	0.935	0.95	1.10	
A1	0.01		0.10	
A2	0.85	0.90	0.925	
Ь	0.30	0.40	0.50	
С	0.10	0.15	0,25	
D	2.70	2.90	3.10	
Ε	2.60	2.80	3.00	
E1	1.40	1.60	1.80	
6	0.95 BSC			
el	1.90 BSC			
L	0.30	0.40	0.60	
L1	0.60REF			
L2	0.25BSC			
R	0.10			
θ	Ű+	4*	8,	
81	7 " N□M			

